www.DataSheet4U.com

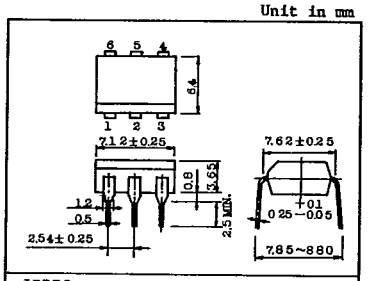
TLP641G

GaAs IRED & PHOTO-THYRISTOR

The TOSHIBA TLP641G consists of a photo-thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

- Peak Off-State Voltage : 400V Min.
- Trigger LED Current : 7mA Max.
- On-State Current : 150mA Max.
- Isolation Voltage : 5000Vrms Min.
- UL Recognized : File No.E67349

Unit in mm

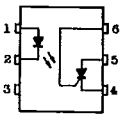


JEDEC	—
EIAJ	—
TOSHIBA	11-7A1

MAXIMUM RATINGS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	RATING	UNIT
LED	Forward Current	I_F	60	mA
	Foward Current Derating (Ta ≧ 39°C)	ΔI_F/°C	-0.7	mA/°C
	Peak Forward Current (100μs pulse, 100pps)	I_{FP}	1	A
	Power Dissipation	P_D	100	mW
	Power Dissipation Derating (Ta ≧ 25°C)	ΔP_D/°C	-1.0	mW/°C
	Reverse Voltage	V_R	5	V
	Junction Temperature	T_j	125	°C
DETECTOR	Peak Forward Voltage (R_{GK}=27KΩ)	V_{DRM}	400	V
	Peak Reverse Voltage (R_{GK}=27KΩ)	V_{RRM}	400	V
	On-State Current	$I_{T(RMS)}$	150	mA
	On-State Current Derating (Ta ≧ 25°C)	ΔI_T/°C	-2.0	mA/°C
	Peak On-State Current (100 s pulse, 120pps)	I_{TP}	3	A
	Peak One Cycle Surge Current	I_{TSM}	2	A
	Peak Reverse Gate Voltage	V_{GM}	5	V
	Power Dissipation	P_D	150	mW
	Power Dissipation Derating (Ta ≧ 25°C)	ΔP_D/°C	-2.0	mW/°C
	Junction Temperature	T_j	100	°C
Storage Temperature Range		T_{stg}	-55 ~ 150	°C
Operating Temperature Range		T_{opr}	-55 ~ 100	°C
Lead Soldering Temperature (10sec.)		T_{sold}	260	°C
Total Package Power Dissipation		P_T	250	mW
Total Package Power Dissipation Derating (Ta ≧ 25°C)		ΔP_T/°C	-3.3	mW/°C
Isolation Voltage (AC, 1 min, RH ≦ 60%)		BV_S	5000	V_{rms}

PIN CONFIGURATIONS (TOP VIEW)



1: ANODE
2: CATHODE
3: NC
4: CATHODE
5: ANODE
6: GATE

COUPLED CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	I_{FT}	V_{AK}=6V, R_{GK}=27kΩ	1	4	7	mA
Turn-on Time	t_{on}	I_F=30mA, V_{AA}=50V R_{GK}=27kΩ	-	10	-	μs
Coupled dv/dt	dv/dt	V_S=500V, R_{GK}=27kΩ	500	-	-	V/μs
Capacitance Input to Output	C_S	V_S=0, f=1MHz	-	0.8	-	pF
Isolation Resistance	R_S	V_S=500V	5×10^{10}	10^{14}	-	Ω
Isolation Voltage	BV_S	AC, 1 minute	5000	-	-	V_{rms}
		AC, 1 second	-	10000	-	
		DC, 1 minute	-	10000	-	V_{dc}

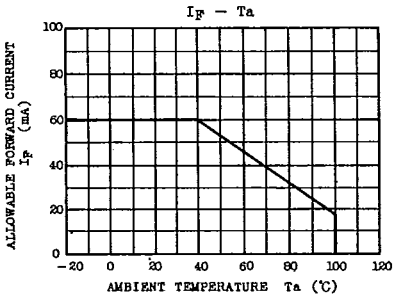
www.DataSheet4U.com

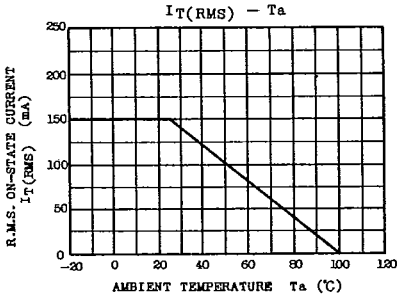
INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta=25°C)

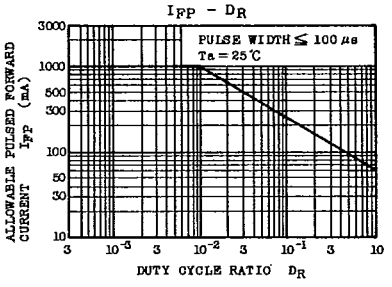
	CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	I_F=10mA		1.0	1.15	1.3	V
	Reverse Current	I_R	V_R=5V		-	-	10	μA
	Capacitance	C_T	V=0, f=1MHz		-	30	-	pF
DETECTOR	Off-State Current	I_{DRM}	V_{AK}=400V, R_{GK}=27kΩ	Ta=25°C	-	10	5000	nA
				Ta=100°C	-	1	100	μA
	Reverse Current	I_{RRM}	V_{KA}=400V, R_{GK}=27kΩ	Ta=25°C	-	10	5000	nA
				Ta=100°C	-	1	100	μA
	On-State Voltage	V_{TM}	I_{TM}=100mA		-	0.9	1.3	V
	Holding Current	I_H	R_{GK}=27kΩ		-	0.2	-	mA
	Off-State dv/dt	dv/dt	V_{AK}=280V, R_{GK}=27kΩ		5	10	-	V/μs
	Capacitance	C_j	V=0, f=1MHz Anode to Gate Gate to Cathode		- -	20 350	- -	pF

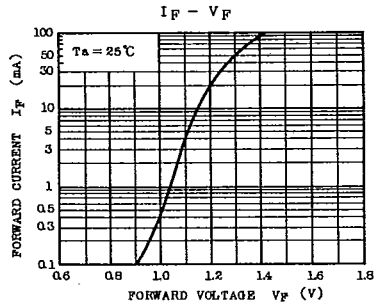
RECOMMENDED OPERATING CONDITIONS

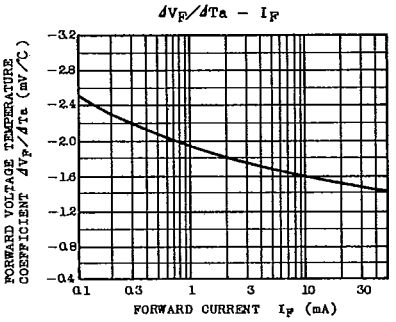
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{AC}	-	-	120	Vac
Forward Current	I_F	14	16	25	mA
Operating Temperature	Topr	-25	-	85	°C
Gate to Cathode Resistance	R_{GK}	-	27	33	kΩ
Gate to Cathode Capacity	C_{GK}	-	0.01	0.1	μF

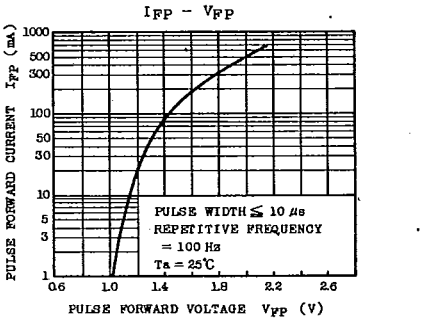












www.DataSheet4U.com